

# 74HC393; 74HCT393

## Dual 4-bit binary ripple counter

Rev. 6 — 3 December 2015

Product data sheet

### 1. General description

The 74HC393; 74HCT393 is a dual 4-stage binary ripple counter. Each counter features a clock input (nCP), an overriding asynchronous master reset input (nMR) and 4 buffered parallel outputs (nQ0 to nQ3). The counter advances on the HIGH-to-LOW transition of nCP. A HIGH on nMR clears the counter stages and forces the outputs LOW, independent of the state of nCP. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V<sub>CC</sub>.

### 2. Features and benefits

- Input levels:
  - ◆ For 74HC393: CMOS level
  - ◆ For 74HCT393: TTL level
- Complies with JEDEC standard no. 7A
- ESD protection:
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V.
- Two 4-bit binary counters with individual clocks
- Divide by any binary module up to 28 in one package
- Two master resets to clear each 4-bit counter individually

### 3. Ordering information

Table 1. Ordering information

Type number	Package				Version
	Temperature range	Name	Description		
74HC393D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm		SOT108-1
74HCT393D					
74HC393DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm		SOT337-1
74HCT393DB					
74HC393PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm		SOT402-1
74HCT393PW					
74HC393BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm		SOT762-1
74HCT393BQ					



#### 4. Functional diagram

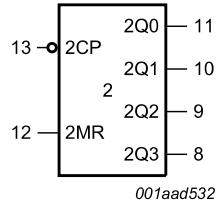
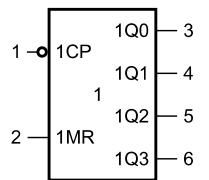


Fig 1. Logic symbol

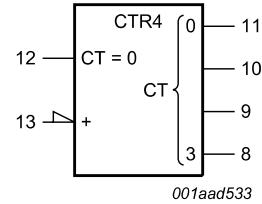
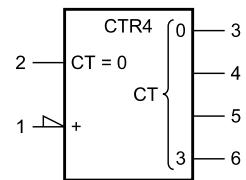


Fig 2. IEC logic symbol

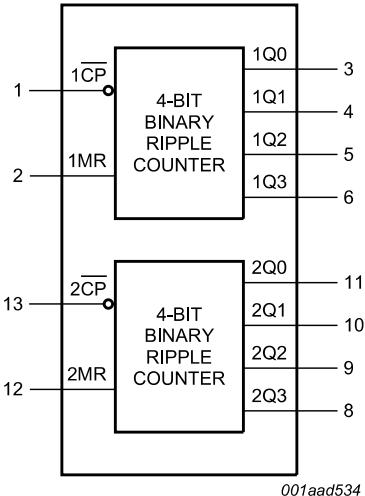


Fig 3. Functional diagram

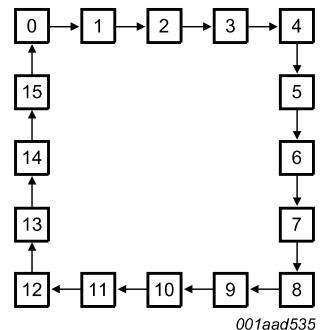


Fig 4. State diagram

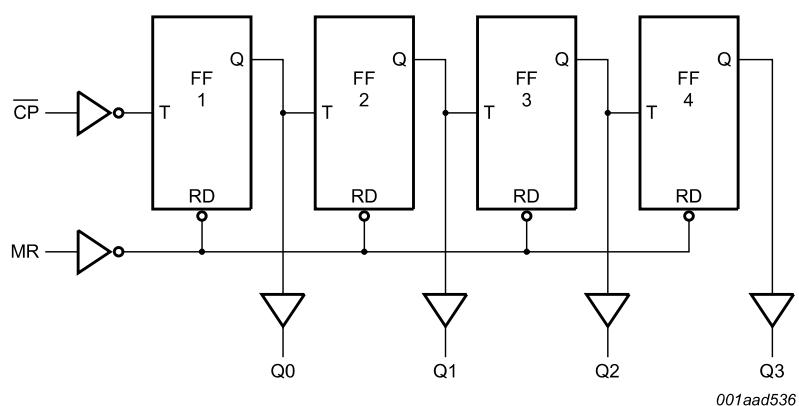


Fig 5. Logic diagram (one counter)

## 5. Pinning information

### 5.1 Pinning

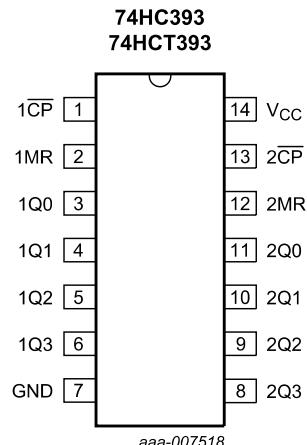


Fig 6. Pin configuration SO14

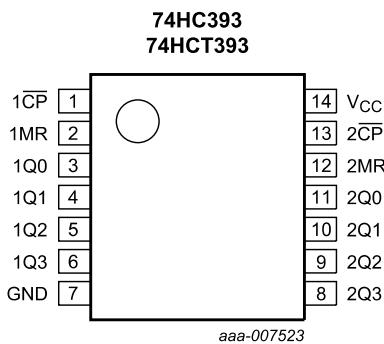


Fig 7. Pin configuration SSOP14 and TSSOP14

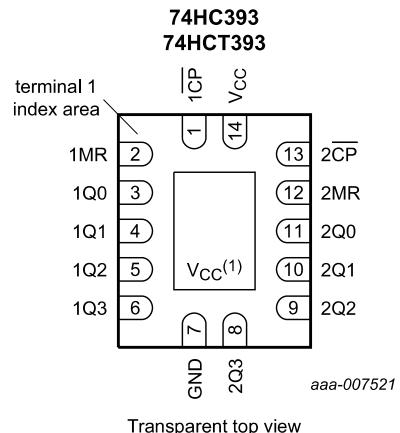


Fig 8. Pin configuration DHVQFN14

- (1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to V<sub>CC</sub>.

## 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1CP	1	clock input (HIGH-to-LOW, edge-triggered)
1MR	2	asynchronous master reset input (active HIGH)
1Q0	3	flip-flop output
1Q1	4	flip-flop output
1Q2	5	flip-flop output
1Q3	6	flip-flop output
GND	7	ground (0 V)
2Q3	8	flip-flop output
2Q2	9	flip-flop output
2Q1	10	flip-flop output
2Q0	11	flip-flop output
2MR	12	asynchronous master reset input (active HIGH)
2CP	13	clock input (HIGH-to-LOW, edge-triggered)
V <sub>CC</sub>	14	supply voltage

## 6. Functional description

**Table 3.** Count sequence for one counter [1]

Count	Output			
	nQ0	nQ1	nQ2	nQ3
0	L	L	L	L
1	H	L	L	L
2	L	H	L	L
3	H	H	L	L
4	L	L	H	L
5	H	L	H	L
6	L	H	H	L
7	H	H	H	L
8	L	L	L	H
9	H	L	L	H
10	L	H	L	H
11	H	H	L	H
12	L	L	H	H
13	H	L	H	H
14	L	H	H	H
15	H	H	H	H

[1] H = HIGH voltage level; L = LOW voltage level.

## 7. Limiting values

**Table 4.** Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V or V <sub>I</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < -0.5 V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>O</sub>	output current	V <sub>O</sub> = -0.5 V to V <sub>CC</sub> + 0.5 V	-	±25	mA
I <sub>CC</sub>	supply current		-	±50	mA
I <sub>GND</sub>	ground current		-	±50	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	SO14, (T)SSOP14 and DHVQFN14 package [1]	-	500	mW

[1] For SO14 package: P<sub>tot</sub> derates linearly with 8 mW/K above 70 °C.

For (T)SSOP14 packages: P<sub>tot</sub> derates linearly with 5.5 mW/K above 60 °C.

For DHVQFN14 packages: P<sub>tot</sub> derates linearly with 4.5 mW/K above 60 °C.

## 8. Recommended operating conditions

**Table 5. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC393			74HCT393			Unit
			Min	Typ	Max	Min	Typ	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V <sub>I</sub>	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 2.0 V	-	-	625	-	-	-	ns/V
		V <sub>CC</sub> = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V <sub>CC</sub> = 6.0 V	-	-	83	-	-	-	ns/V

## 9. Static characteristics

**Table 6. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74HC393</b>										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I <sub>O</sub> = −4.0 mA; V <sub>CC</sub> = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I <sub>O</sub> = −5.2 mA; V <sub>CC</sub> = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I <sub>O</sub> = 5.2 mA; V <sub>CC</sub> = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V	-	-	±0.1	-	±0.1	-	±0.1	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	8.0	-	80	-	160	μA

**Table 6. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C <sub>I</sub>	input capacitance		-	3.5	-	-	-	-	-	pF
<b>74HCT393</b>										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = −20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = −6 mA	3.98	4.32	-	3.84	-	3.7	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 6.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	8.0	-	80	-	160	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> − 2.1 V; other inputs at V <sub>CC</sub> or GND; V <sub>CC</sub> = 4.5 V to 5.5 V; I <sub>O</sub> = 0 A								
		per input pin; nCP	-	40	144	-	180	-	196	μA
		per input pin; nMR	-	100	360	-	450	-	490	μA
C <sub>I</sub>	input capacitance		-	3.5	-	-	-	-	-	pF

## 10. Dynamic characteristics

**Table 7. Dynamic characteristics**Voltages are referenced to GND (ground = 0 V);  $C_L = 50 \text{ pF}$  unless otherwise specified; for test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74HC393</b>										
$t_{pd}$	propagation delay	nCP to nQ0; see <a href="#">Figure 9</a> [1]								
		$V_{CC} = 2.0 \text{ V}$	-	41	125	-	155	-	190	ns
		$V_{CC} = 4.5 \text{ V}$	-	15	25	-	31	-	38	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	12	-	-	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}$	-	12	21	-	26	-	32	ns
		nQx to nQ(x+1); see <a href="#">Figure 9</a> [1]								
		$V_{CC} = 2.0 \text{ V}$	-	14	45	-	55	-	70	ns
		$V_{CC} = 4.5 \text{ V}$	-	5	9	-	11	-	14	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	5	-	-	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}$	-	4	8	-	9	-	12	ns
$t_{PHL}$	HIGH to LOW propagation delay	nMR to nQx; see <a href="#">Figure 10</a>								
		$V_{CC} = 2.0 \text{ V}$	-	39	140	-	175	-	210	ns
		$V_{CC} = 4.5 \text{ V}$	-	14	28	-	35	-	42	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	11	-	-	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}$	-	11	24	-	30	-	36	ns
$t_t$	transition time	Qn; see <a href="#">Figure 9</a> [2]								
		$V_{CC} = 2.0 \text{ V}$	-	19	75	-	95	-	110	ns
		$V_{CC} = 4.5 \text{ V}$	-	7	15	-	19	-	22	ns
		$V_{CC} = 6.0 \text{ V}$	-	6	13	-	16	-	19	ns
$t_w$	pulse width	nCP HIGH or LOW; see <a href="#">Figure 9</a>								
		$V_{CC} = 2.0 \text{ V}$	80	17	-	100	-	120	-	ns
		$V_{CC} = 4.5 \text{ V}$	16	6	-	20	-	24	-	ns
		$V_{CC} = 6.0 \text{ V}$	14	5	-	17	-	20	-	ns
		nMR HIGH; see <a href="#">Figure 10</a>								
		$V_{CC} = 2.0 \text{ V}$	80	19	-	100	-	120	-	ns
		$V_{CC} = 4.5 \text{ V}$	16	7	-	20	-	24	-	ns
		$V_{CC} = 6.0 \text{ V}$	14	6	-	17	-	20	-	ns
		nMR to nCP; see <a href="#">Figure 10</a>								
		$V_{CC} = 2.0 \text{ V}$	5	3	-	5	-	5	-	ns
$t_{rec}$	recovery time	$V_{CC} = 4.5 \text{ V}$	5	1	-	5	-	5	-	ns
		$V_{CC} = 6.0 \text{ V}$	5	1	-	5	-	5	-	ns

**Table 7. Dynamic characteristics ...continued**Voltages are referenced to GND (ground = 0 V);  $C_L = 50 \text{ pF}$  unless otherwise specified; for test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
$f_{\text{clk(max)}}$	maximum clock frequency	see <a href="#">Figure 9</a>								
		$V_{\text{CC}} = 2.0 \text{ V}$	6	30	-	5	-	4	-	MHz
		$V_{\text{CC}} = 4.5 \text{ V}$	30	90	-	24	-	20	-	MHz
		$V_{\text{CC}} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	99	-	-	-	-	-	MHz
		$V_{\text{CC}} = 6.0 \text{ V}$	35	107	-	28		24	-	MHz
$C_{\text{PD}}$	power dissipation capacitance	$C_L = 50 \text{ pF}; f = 1 \text{ MHz}; V_I = \text{GND to } V_{\text{CC}}$	[3]	-	23	-	-	-	-	pF
<b>74HCT393</b>										
$t_{\text{pd}}$	propagation delay	$n\bar{C}\bar{P}$ to $nQ0$ ; see <a href="#">Figure 9</a> [1]								
		$V_{\text{CC}} = 4.5 \text{ V}$	-	15	25	-	31	-	38	ns
		$V_{\text{CC}} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	20	-	-	-	-	-	ns
		$nQx$ to $nQ(x+1)$ ; see <a href="#">Figure 9</a> [1]								
		$V_{\text{CC}} = 4.5 \text{ V}$	-	6	10	-	13	-	15	ns
		$V_{\text{CC}} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	6	-	-	-	-	-	ns
$t_{\text{PHL}}$	HIGH to LOW propagation delay	$nM\bar{R}$ to $nQx$ ; see <a href="#">Figure 10</a>								
		$V_{\text{CC}} = 4.5 \text{ V}$	-	18	32	-	40	-	48	ns
		$V_{\text{CC}} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	15	-	-	-	-	-	ns
$t_t$	transition time	$Qn$ ; see <a href="#">Figure 9</a> [2]								
		$V_{\text{CC}} = 4.5 \text{ V}$	-	7	15	-	19	-	22	ns
$t_w$	pulse width	$n\bar{C}\bar{P}$ HIGH or LOW; see <a href="#">Figure 9</a>								
		$V_{\text{CC}} = 4.5 \text{ V}$	19	11	-	24	-	29	-	ns
		$nM\bar{R}$ HIGH; see <a href="#">Figure 10</a>								
		$V_{\text{CC}} = 4.5 \text{ V}$	16	6	-	20	-	24	-	ns
$t_{\text{rec}}$	recovery time	$nM\bar{R}$ to $n\bar{C}\bar{P}$ ; see <a href="#">Figure 10</a>								
		$V_{\text{CC}} = 4.5 \text{ V}$	5	0	-	5	-	5	-	ns
$f_{\text{clk(max)}}$	maximum clock frequency	see <a href="#">Figure 9</a>								
		$V_{\text{CC}} = 4.5 \text{ V}$	27	48	-	22	-	18	-	MHz
		$V_{\text{CC}} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	53	-	-	-	-	-	MHz

**Table 7. Dynamic characteristics ...continued**Voltages are referenced to GND (ground = 0 V);  $C_L = 50 \text{ pF}$  unless otherwise specified; for test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
$C_{PD}$	power dissipation capacitance	$C_L = 50 \text{ pF}; f = 1 \text{ MHz}; V_I = \text{GND to } V_{CC} - 1.5 \text{ V}$ [3]	-	25	-	-	-	-	-	pF

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .[2]  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .[3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu\text{W}$ ).

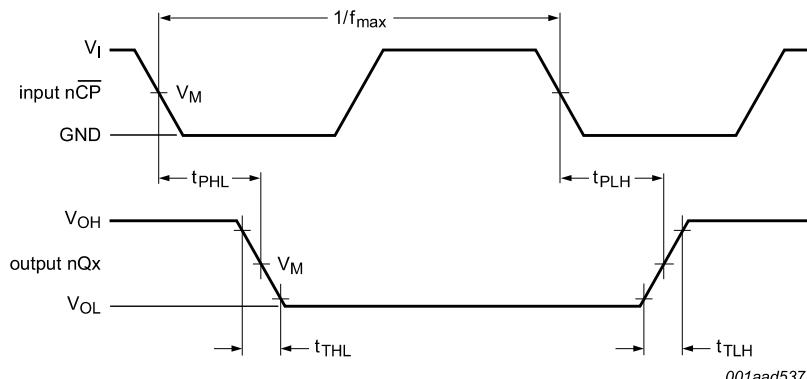
$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

 $f_i$  = input frequency in MHz; $f_o$  = output frequency in MHz; $C_L$  = output load capacitance in pF; $V_{CC}$  = supply voltage in V;

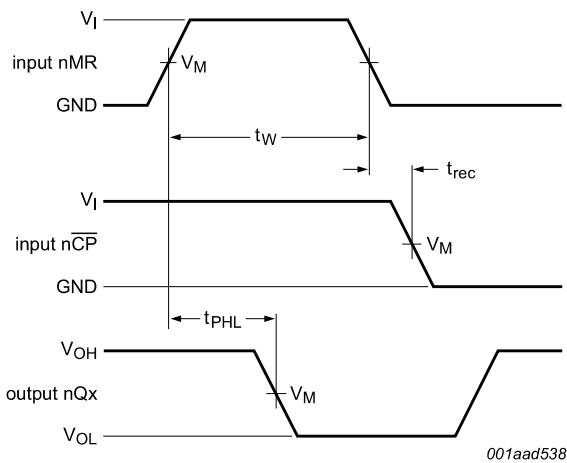
N = number of inputs switching;

 $\sum(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

## 10.1 Waveforms

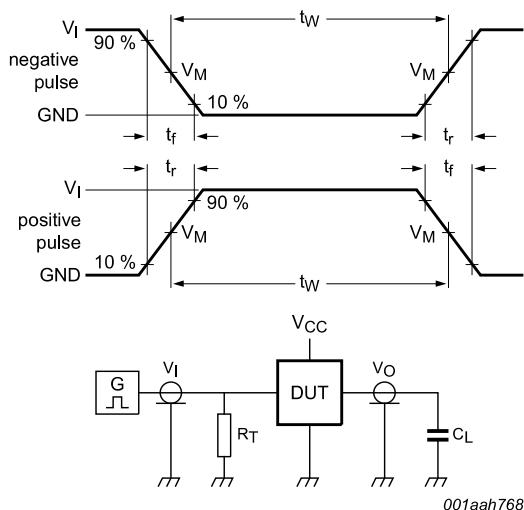
Measurement points are given in [Table 8](#).**Fig 9. Propagation delays clock (nCP) to output (nQx), the output transition times and the maximum clock frequency****Table 8. Measurement points**

Type	Input		Output	
	$V_M$	$V_M$	$V_M$	$V_M$
74HC393	0.5 $V_{CC}$		0.5 $V_{CC}$	
74HCT393	1.3 V		1.3 V	



Measurement points are given in [Table 8](#).

**Fig 10.** Propagation delays clock ( $nCP$ ) to output ( $nQx$ ), pulse width master reset ( $nMR$ ), and recovery time master reset ( $nMR$ ) to clock ( $nCP$ )



Test data is given in [Table 9](#).

Definitions test circuit:

$R_T$  = termination resistance should be equal to output impedance  $Z_0$  of the pulse generator.

$C_L$  = load capacitance including jig and probe capacitance.

**Fig 11.** Test circuit for measuring switching times

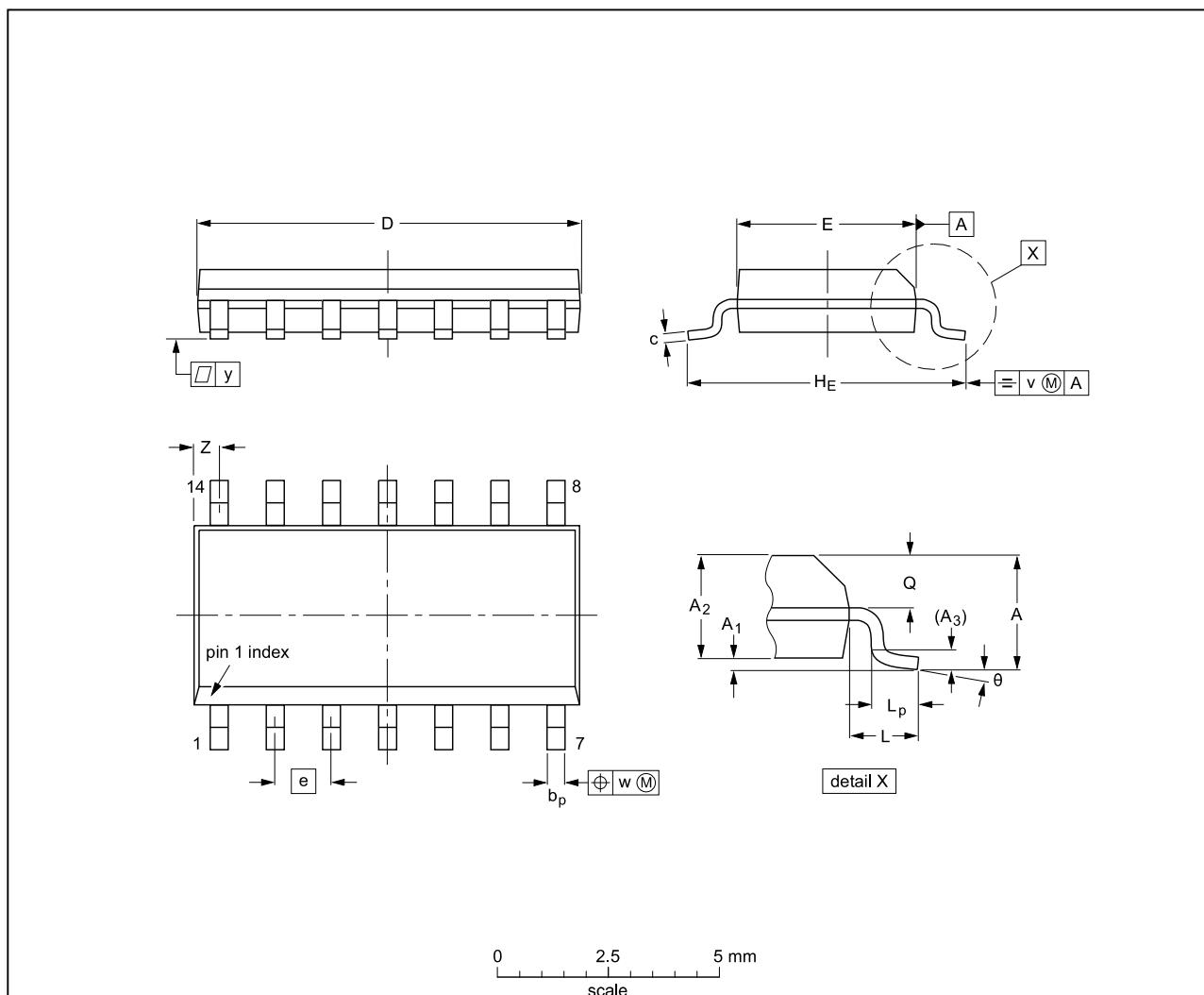
**Table 9.** Test data

Type	Input		Load	Test
	$V_I$	$t_r, t_f$		
74HC393	$V_{CC}$	6.0 ns	15 pF, 50 pF	$t_{PLH}, t_{PHL}$
74HCT393	3.0 V	6.0 ns	15 pF, 50 pF	$t_{PLH}, t_{PHL}$

## 11. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



**DIMENSIONS** (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(1)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	Z <sup>(1)</sup>	θ
mm	1.75 0.10	0.25 1.25	1.45	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069 0.004	0.010 0.049	0.057	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

**Note**

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT108-1	076E06	MS-012				99-12-27 03-02-19

**Fig 12. Package outline SOT108-1 (SO14)**

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1

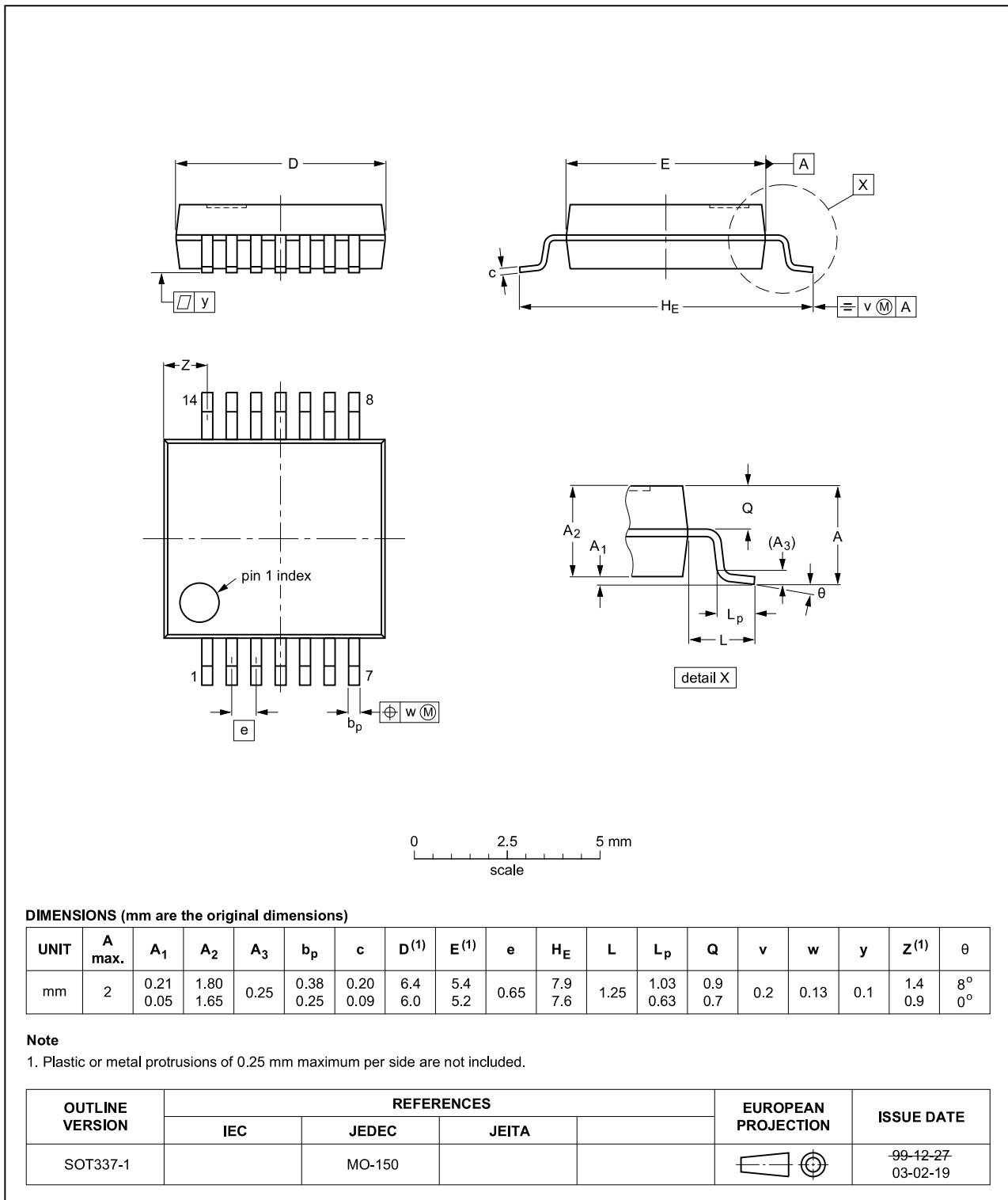


Fig 13. Package outline SOT337-1 (SSOP14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

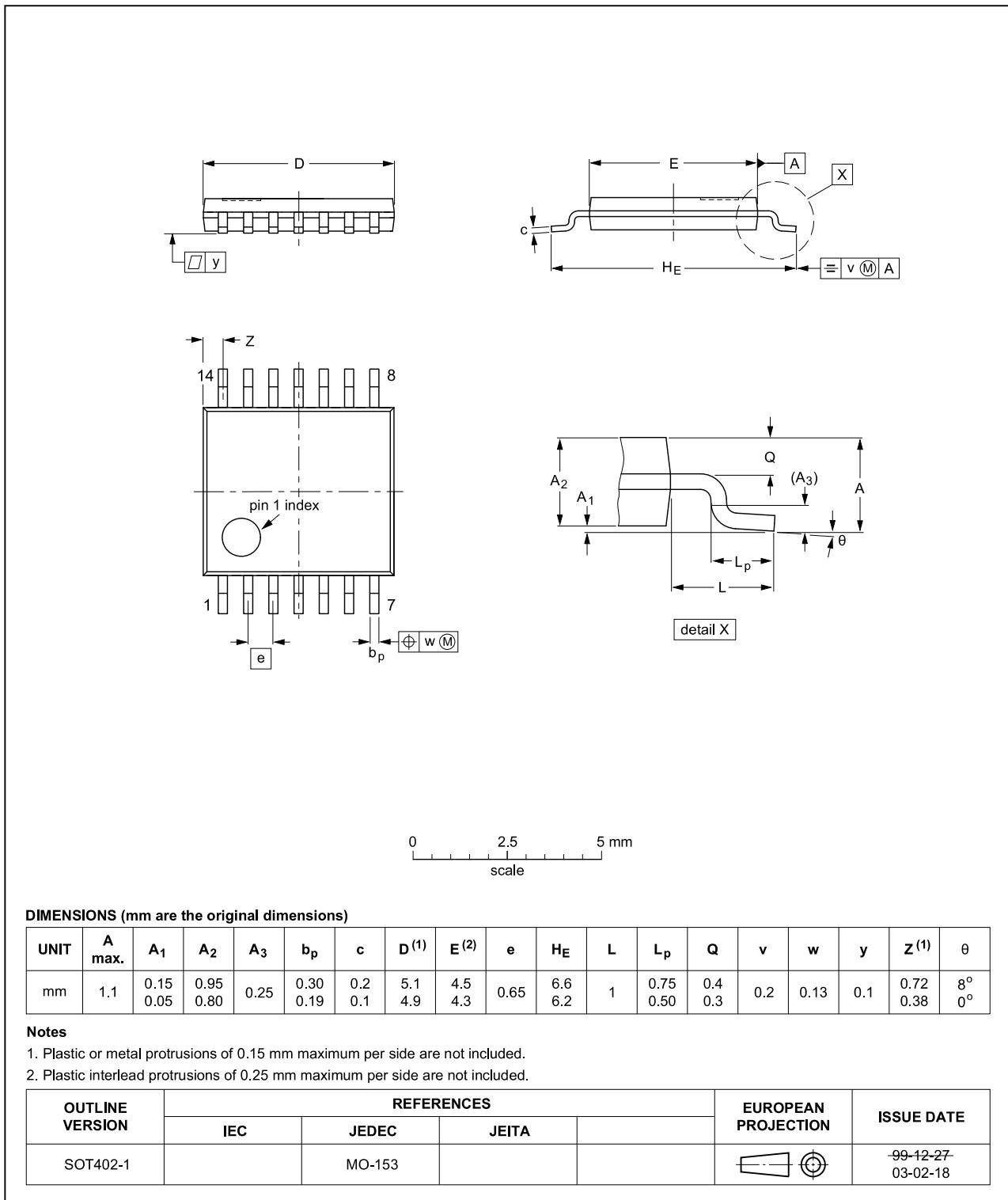


Fig 14. Package outline SOT402-1 (TSSOP14)